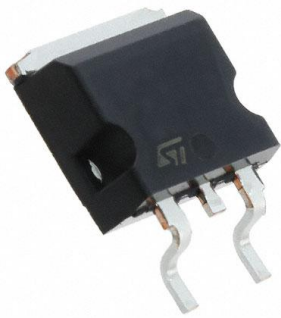


STB45N30M5 Datasheet

www.digi-electronics.com



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DiGi Electronics Part Number	STB45N30M5-DG
Manufacturer	STMicroelectronics
Manufacturer Product Number	STB45N30M5
Description	NCHANNEL 300 V 0.037 OHM TYP. 53
Detailed Description	N-Channel 300 V 53A (Tc) 250W (Tc) Surface Mount TO-263 (D2PAK)

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Purchase and inquiry

Manufacturer Product Number:

STB45N30M5

Series:

MDmesh™ M5

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

300 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

5V @ 250μA

Vgs (Max):

±25V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-263 (D2PAK)

Base Product Number:

STB45

Manufacturer:

STMicroelectronics

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

53A (Tc)

Rds On (Max) @ Id, Vgs:

40mOhm @ 26.5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

95 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

4240 pF @ 100 V

Power Dissipation (Max):

250W (Tc)

Mounting Type:

Surface Mount

Package / Case:

TO-263-3, D2PAK (2 Leads + Tab), TO-263AB

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

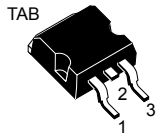
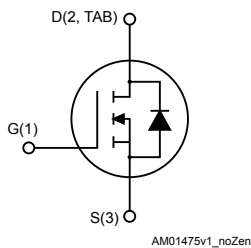
Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

N-channel 300 V, 53 A, 0.037 Ω typ., MDmesh™ M5 Power MOSFET in a D²PAK package

D²PAK

Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STB45N30M5	300 V	0.040 Ω	53 A

- Extremely low R_{DS(on)}
- Low gate charge and input capacitance
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET based on the MDmesh™ M5 innovative vertical process technology combined with the well-known PowerMESH™ horizontal layout. The resulting product offers extremely low on-resistance, making it particularly suitable for applications requiring high power and superior efficiency.

Product status link

[STB45N30M5](#)

Product summary

Order code	STB45N30M5
Marking	45N30M5
Package	D ² PAK
Packing	Tape and reel



1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ °C}$	53	A
	Drain current (continuous) at $T_{case} = 100\text{ °C}$	34	
$I_{DM}^{(1)}$	Drain current (pulsed)	212	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ °C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2. $I_{SD} \leq 53\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 240\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	30	

1. When mounted on an 1-inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by $T_j\text{ max}$)	16	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	550	mJ



2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified

Table 4. On-/off-states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	300			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 300\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 300\text{ V}$, $T_C = 125\text{ }^\circ\text{C}^{(1)}$			100	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 26.5\text{ A}$		0.037	0.040	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	4240	-	pF
C_{oss}	Output capacitance		-	205	-	pF
C_{riss}	Reverse transfer capacitance		-	9.5	-	pF
$C_{o(tr)}^{(1)}$	Time-related equivalent capacitance	$V_{DS} = 0\text{ to }240\text{ V}$, $V_{GS} = 0\text{ V}$	-	373	-	pF
$C_{o(er)}^{(2)}$	Energy-related equivalent capacitance		-	202	-	pF
R_G	Gate input resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1.4	-	Ω
Q_g	Total gate charge	$V_{DD} = 240\text{ V}$, $I_D = 24\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)	-	95	-	nC
Q_{gs}	Gate-source charge		-	23	-	nC
Q_{gd}	Gate-drain charge		-	37	-	nC

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

2. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 240\text{ V}$, $I_D = 32\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times and Figure 19. Switching time waveform)	-	66	-	ns
$t_{r(v)}$	Voltage rise time		-	15	-	ns
$t_{f(i)}$	Current fall time		-	24	-	ns
$t_{c(off)}$	Crossing time		-	22.5	-	ns


Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		53	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		212	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 53 \text{ A}$, $V_{GS} = 0 \text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 48 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$	-	223		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current	(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	23		A
t_{rr}	Reverse recovery time	$I_{SD} = 48 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$	-	280		ns
Q_{rr}	Reverse recovery charge		-	3.9		μC
I_{RRM}	Reverse recovery current		(see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	28	

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%



2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

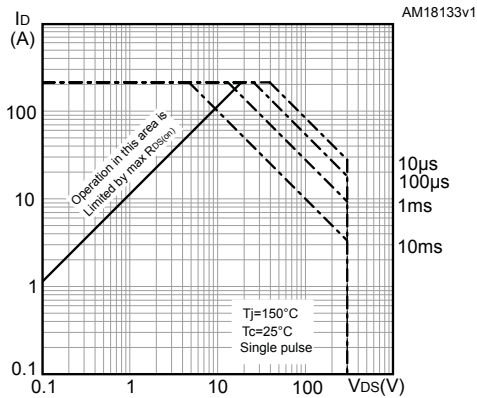


Figure 2. Thermal impedance

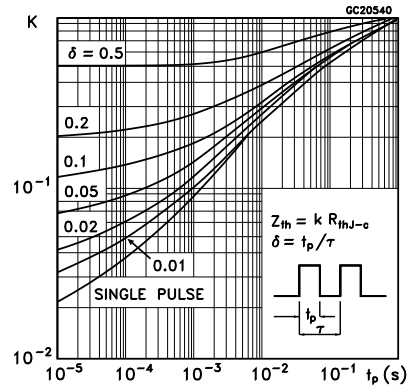


Figure 3. Output characteristics

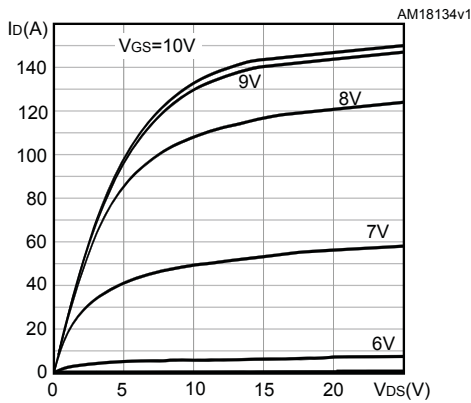


Figure 4. Transfer characteristics

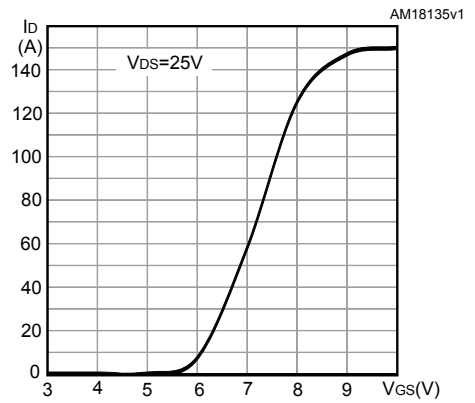


Figure 5. Gate charge vs gate-source voltage

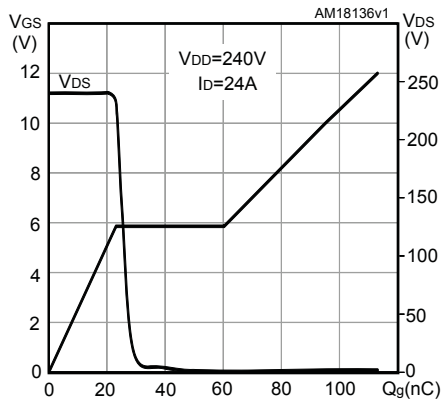


Figure 6. Static drain-source on-resistance

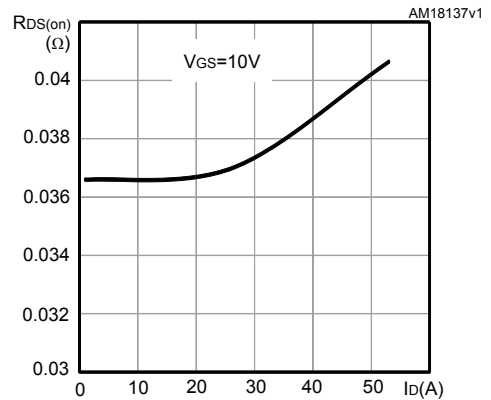




Figure 7. Capacitance variations

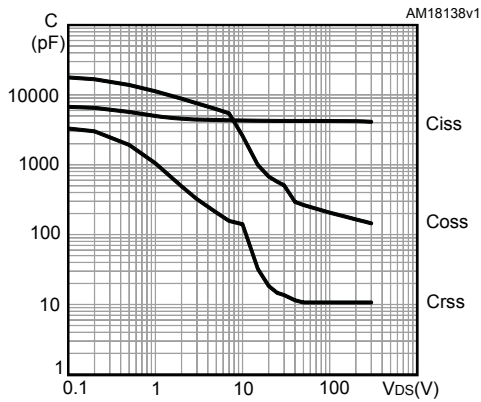


Figure 8. Output capacitance stored energy

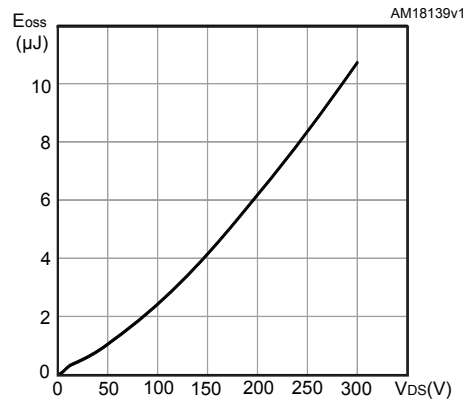


Figure 9. Normalized gate threshold voltage vs temperature

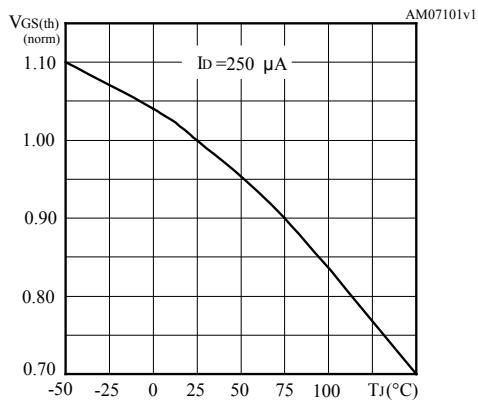


Figure 10. Normalized on-resistance vs temperature

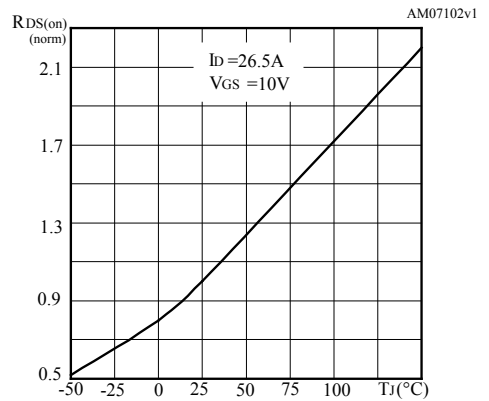


Figure 11. Normalized V(BR)DSS vs temperature

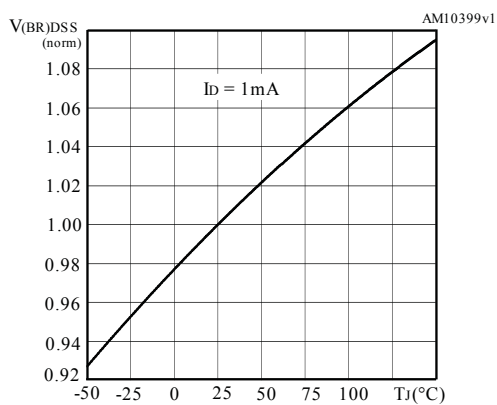


Figure 12. Source-drain diode forward characteristics

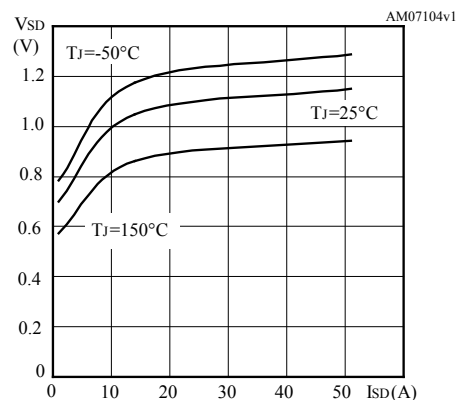
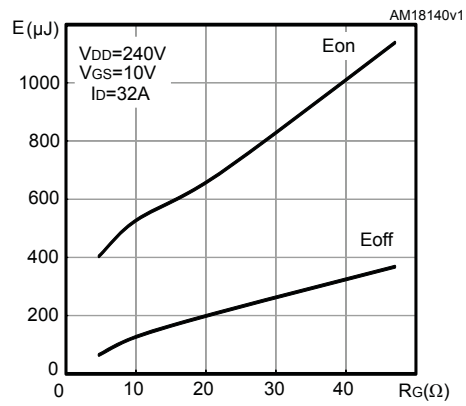
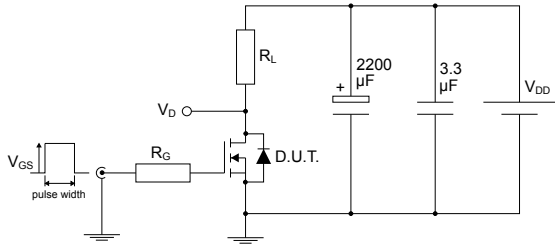


Figure 13. Switching energy vs gate resistance



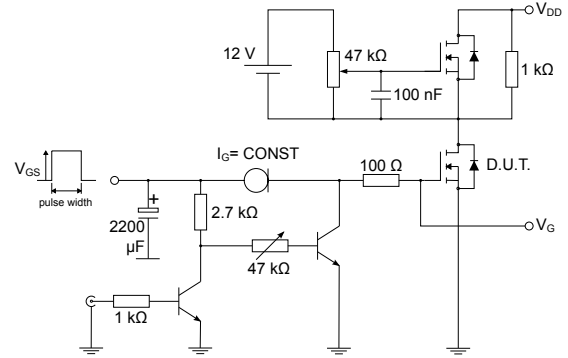
3 Test circuits

Figure 14. Test circuit for resistive load switching times



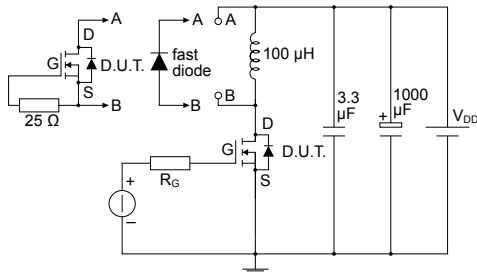
AM01488v1

Figure 15. Test circuit for gate charge behavior



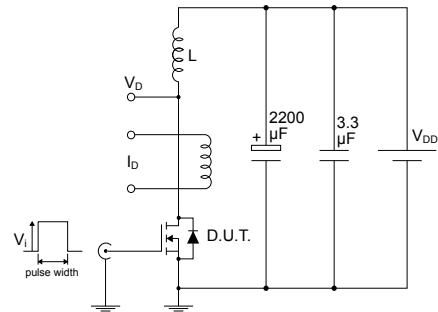
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Figure 16. Test circuit for inductive load switching and diode recovery times



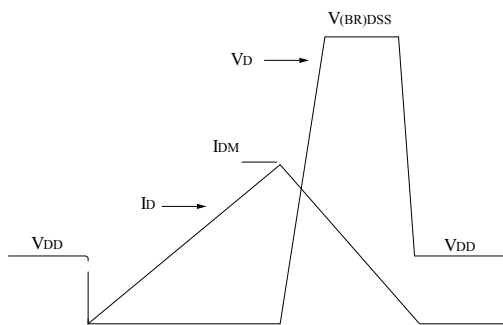
AM01470v1

Figure 17. Unclamped inductive load test circuit



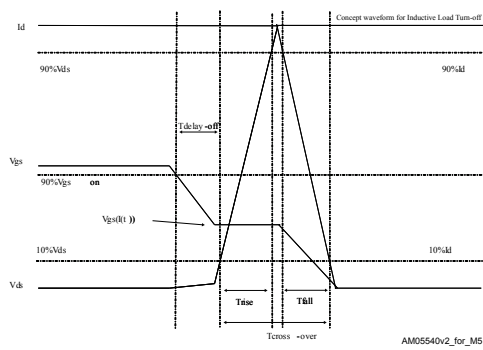
AM01471v1

Figure 18. Unclamped inductive waveform



AM01472v1

Figure 19. Switching time waveform



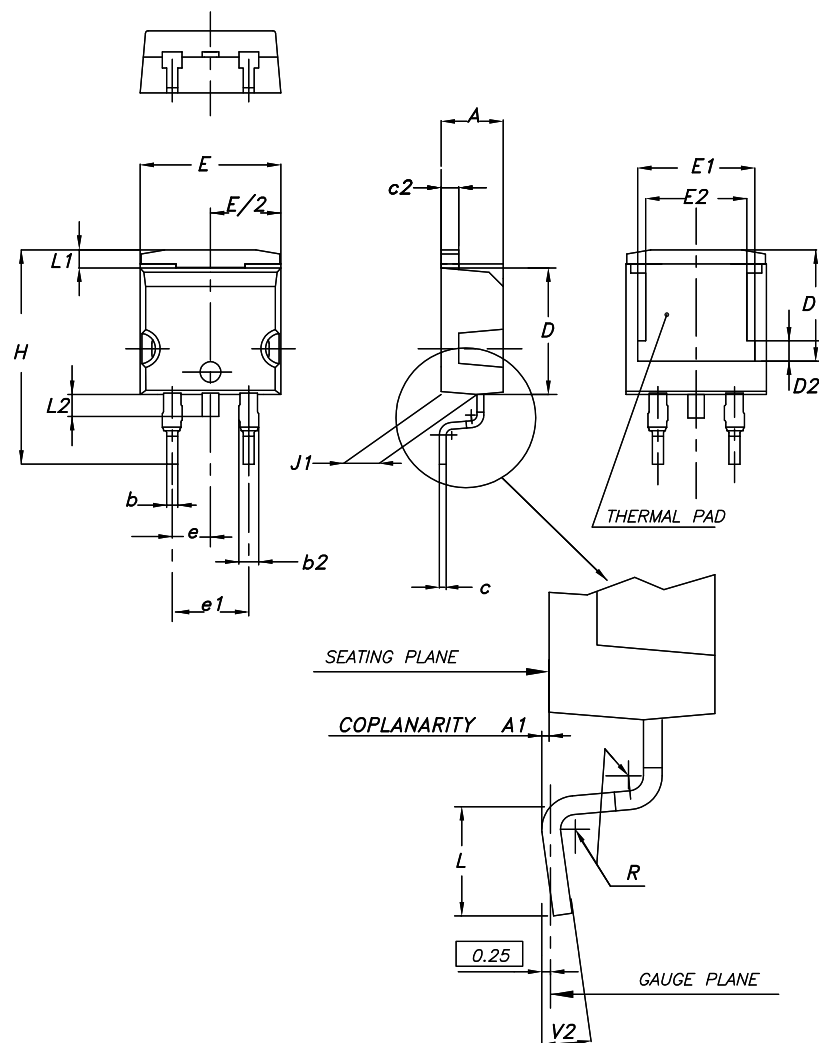
AM05540v2_for_M5

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) type A2 package information

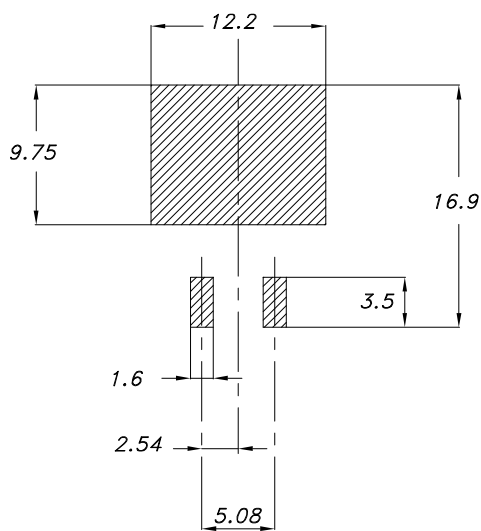
Figure 20. D²PAK (TO-263) type A2 package outline



0079457_A2_24

Table 8. D²PAK (TO-263) type A2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.70	8.90	9.10
E2	7.30	7.50	7.70
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

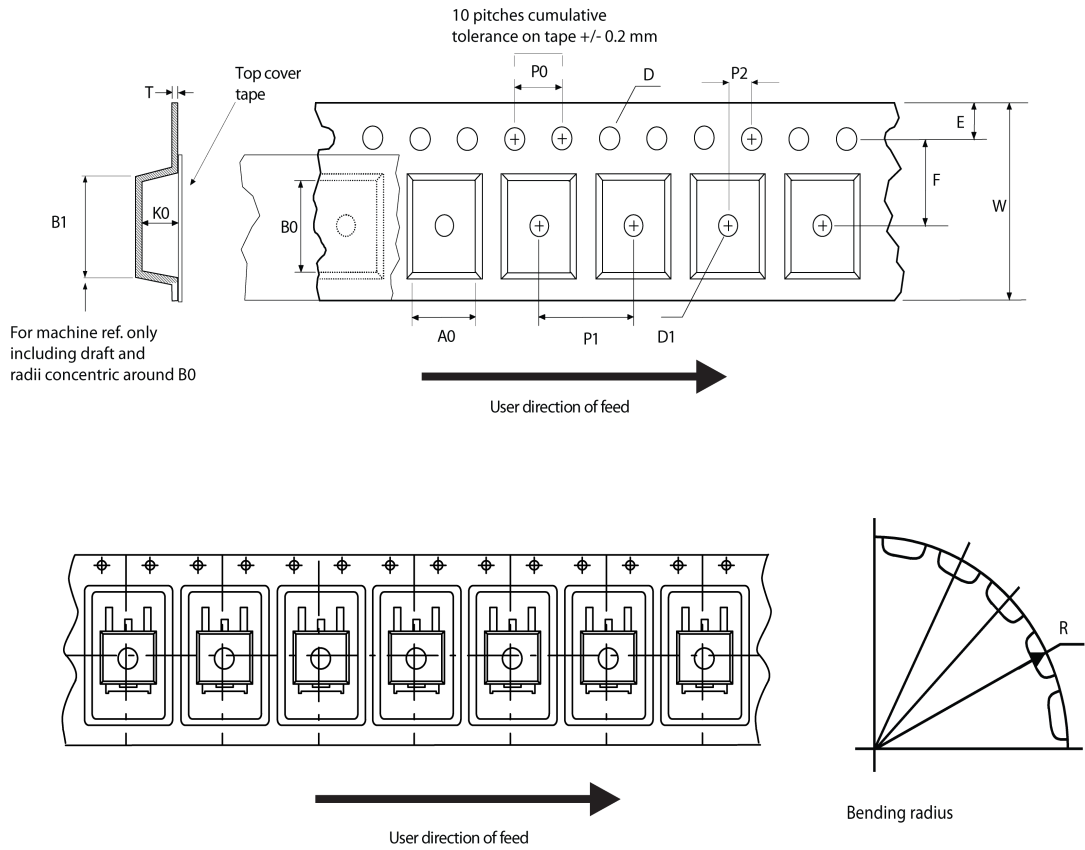
Figure 21. D²PAK (TO-263) recommended footprint (dimensions are in mm)

Footprint

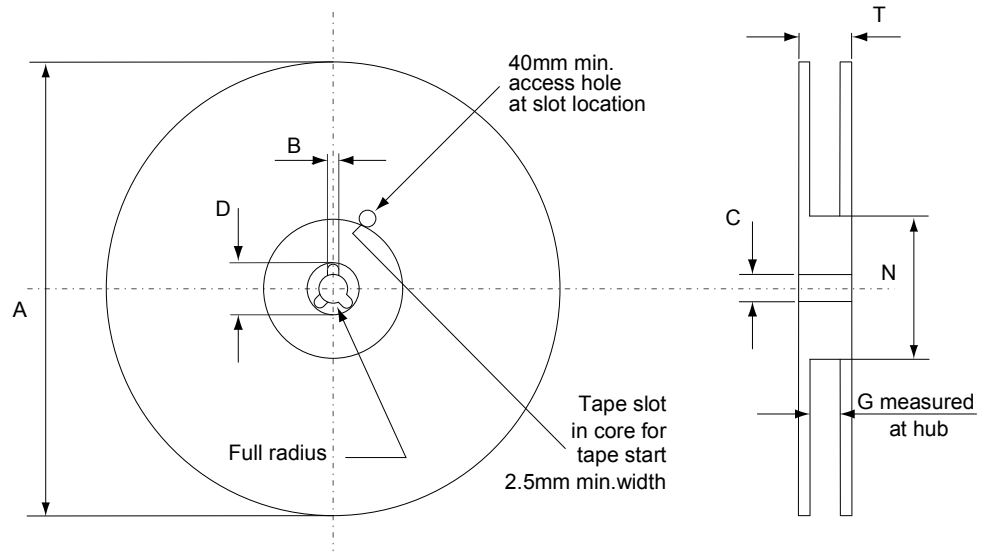


4.2 D²PAK packing information

Figure 22. D²PAK tape outline



AM08852v1

Figure 23. D²PAK reel outline


AM06038v1

Table 9. D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			



Revision history

Table 10. Document revision history

Date	Version	Changes
16-May-2018	1	Initial release



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